IN THE SPECIFICATION

Replace the paragraph on page 3, line 21 through page 4 line 8, with the following paragraph:

~~U.S. Application No. 09/740,701 entitled~~ U.S. Patent No. 6,534,116 for "Plating Method and Apparatus that Creates a Differential Between Additive Disposed on a Top Surface and a Cavity Surface of a Workpiece Using an External Influence," also assigned to the same assignee as the present invention, describes in one aspect another ECMD method and apparatus for plating a conductive material onto the substrate by creating an external influence, such as causing relative movement between a workpiece and a mask, to cause a differential in additives to exist for a period of time between a top surface and a cavity surface of a workpiece. While the differential is maintained, power is applied between an electrode (in this case anode) and the substrate to cause greater relative plating of the cavity surface than the top surface.

Replace the paragraph on page 13, lines 6-13, with the following paragraph:

It should be understood that ECMD, ECME, and other processes can occur in succession, and that any number of such processes can occur, with a conditioning step occurring thereafter, and then any number of such processes can occur again. For example, an ECMD process, followed by an ECME process, followed by an ECMD process is typical. It may then be desirable to perform conditioning of the WSID according to the present invention, and then resume with some number of processes, for instance another set of ECMD, ECME, and ECMD processes. Alternately, conditioning may be done after the ECMD process before the ~~EMME~~ ECME process, etc.

Replace the paragraph on page 20, line 9 through page 21 line 2, with the following paragraph:

Referring back to Figure 14,the system 300 comprises a lower chamber 302, an upper chamber 304 and a carrier head 305 holding the wafer. The lower chamber 302 is comprised of a chamber that includes an electro chemical mechanical processing (ECMPR) unit 306. The ECMPR unit 306 comprises an electrode 308 and a WSID 400. As mentioned before, during processing, an electrolyte solution 312 contacts the electrode 308 and flows onto and through the WSID 400. Description of aspects of one such system can be found in ~~the pending US Application No. 09/466,014 entitled~~ U.S. Patent No. 6,532,623 for "A Vertically Configured Chamber Used For Multiple Processes" which is commonly owned by the assignee of the present invention The conditioning device is also incorporated in the ECMPR unit 306. The upper chamber 304 is separated from the lower chamber 302 by movable guards or flaps 314. In this embodiment, the wafer is loaded in the upper chamber 304 and lowered into the lower chamber 302 for ECMPR. Once the ECMPR is over, the carrier head retaining the wafer is raised into the upper chamber 304 and the flaps 314 are closed. While the wafer is rinsed and dried in the upper chamber 304, the WSID is conditioned in the lower chamber 302 using a brush member 250.